



STY16NA90

N - CHANNEL 900V - 0.5 Ω - 16A - Max247 EXTREMELY LOW GATE CHARGE POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STY16NA90	900 V	< 0.54 Ω	16 A

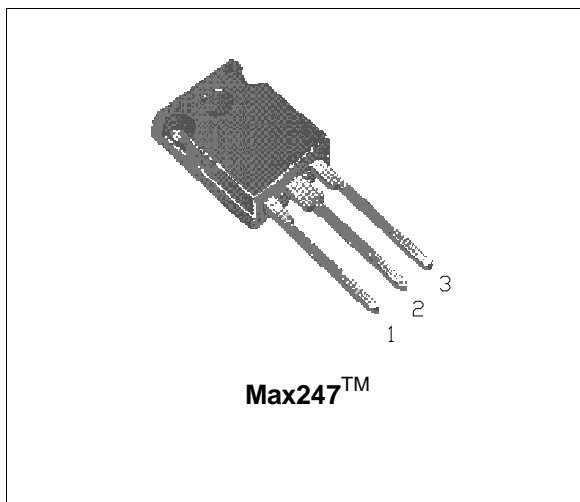
- TYPICAL R_{DS(on)} = 0.5 Ω
- EFFICIENT AND RELIABLE MOUNTING THROUGH CLIP
- ± 30 V GATE TO SOURCE VOLTAGE RATING
- REPETITIVE AVALANCHE TESTED
- LOW INTRINSIC CAPACITANCE
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

DESCRIPTION

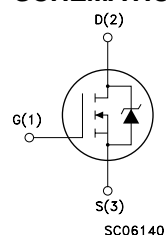
The Max247™ package is a new high volume power package exhibiting the same footprint as the industry standard TO-247, but designed to accommodate much larger silicon chips, normally supplied in bigger packages such as TO-264. The increased die capacity makes the device ideal to reduce component count in multiple paralleled designs and save board space with respect to larger packages.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES (UPS)



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	900	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 k Ω)	900	V
V _{GS}	Gate-source Voltage	± 30	V
I _D	Drain Current (continuous) at T _c = 25 °C	16	A
I _D	Drain Current (continuous) at T _c = 100 °C	10	A
I _{DM} (•)	Drain Current (pulsed)	64	A
P _{tot}	Total Dissipation at T _c = 25 °C	300	W
	Derating Factor	2.4	W/°C
T _{stg}	Storage Temperature	-55 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

STY16NA90

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.42	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	40	°C/W
R _{thc-sink}	Thermal Resistance Case-Heatsink with Conductive Grease	Typ	0.05	

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	16	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	3000	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	900			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			50 500	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	2.25	3	3.75	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 8 A		0.5	0.54	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	16			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 8 A	15			S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		6400 600 150	8300 750 200	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 450\text{ V}$		30		ns
t_r	Rise Time	$I_D = 8\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		30		ns
Q_g	Total Gate Charge	$V_{DD} = 720\text{ V}$ $I_D = 16\text{ A}$ $V_{GS} = 10\text{ V}$		245	320	nC
Q_{gs}	Gate-Source Charge			25		nC
Q_{gd}	Gate-Drain Charge			110		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 720\text{ V}$		80	105	ns
t_f	Fall Time	$I_D = 16\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		25	35	ns
t_c	Cross-over Time			115	150	ns

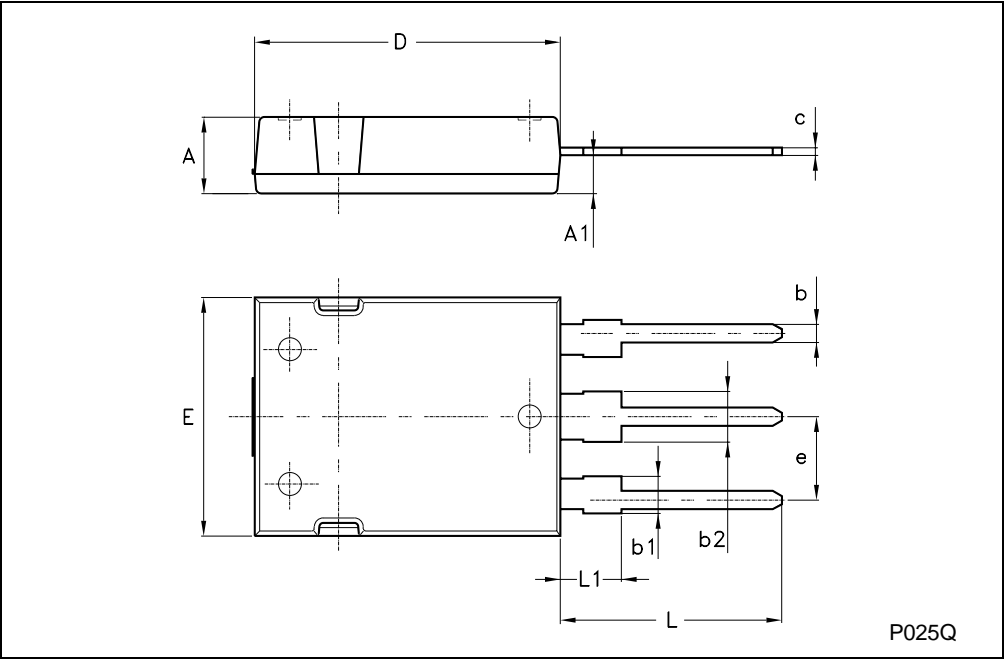
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				16	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				64	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 16\text{ A}$ $V_{GS} = 0$			2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 16\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		1100		ns
Q_{rr}	Reverse Recovery Charge			25.3		μC
I_{RRM}	Reverse Recovery Current			46		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Max247 MECHANICAL DATA						
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.70		5.30			
A1	2.20		2.60			
b	1.00		1.40			
b1	2.00		2.40			
b2	3.00		3.40			
c	0.40		0.80			
D	19.70		20.30			
e	5.35		5.55			
E	15.30		15.90			
L	14.20		15.20			
L1	3.70		4.30			



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